

Remarks:

The purpose of the amendment is to correct a minor error in the specification.

The application includes Figs. 2a-2e. The specification incorrectly stated that there are Figs. 2a-2f. The specification has been amended to correspond to the drawings. A petition and fee under 37 CFR 1.17(i) is therefore not necessary.

The Notice to File Missing Parts states that fees for additional claims have not been paid. The application was filed with a check in the amount of \$844.00. This amount covers the filing fee (\$710.00) and the fees for additional claims (\$134). A copy of the cancelled check is enclosed. It is therefore believed that no additional fees for claims are due.

Applicants still need to file the signed oath or declaration.

An early action on the merits of the application is solicited.

Respectfully submitted,

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For Applicants

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Marked-Up Version of the Amended Paragraphs in the
Specification:

Marked-up the paragraph on page 20, lines 12-14:

-- Figs. 2a to [2f] 2e are partial, diagrammatic sectional views of structures illustrating further process steps for fabricating a microelectronic structure; --

Marked-up the paragraph on page 25, lines 2-14:

-- Process steps for fabricating a microelectronic structure with a metal silicide layer on the base substrate in accordance with a further exemplary embodiment are illustrated in Figs. 2a to [2f] 2e. In this case, too, the process proceeds from a base substrate 5, which may optionally also be constructed from two layers. To that end, the base substrate 5 includes a lower silicon dioxide layer 50 with a silicon nitride or TEOS layer 55 situated above it. The base substrate 5 furthermore has a contact hole 10, which is filled with polysilicon up to the surface 15 of the base substrate 5. First of all, after cleaning with hydrofluoric acid, a platinum, titanium or cobalt silicide layer having a thickness of between 30 and 100 nm is applied to this structure illustrated in Fig. 2a. --